

Title (en)
SEMICONDUCTOR MEMORY DEVICE

Publication
EP 0194939 B1 19920205 (EN)

Application
EP 86400504 A 19860311

Priority
• JP 4935085 A 19850314
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Abstract (en)
[origin: EP0194939A2] A semiconductor memory device of multi-bit type which produces plural output signals (O_{1} , ..., O_{8}) corresponding to read-out data from one address at a time including memory means for storing data. In a plurality of output buffer stages for producing the output signals, the operation of the output buffer stages is based upon at least a timing signal. Means (151, ..., 158) for operating the output buffer stages have predetermined time differences. The output signals (O_{1} , .. O_{8}) having predetermined time differences are delivered from the output buffer stages.

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G11C 7/00

IPC 8 full level
G11C 7/10 (2006.01); **G11C 7/22** (2006.01)

CPC (source: EP KR US)
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G11C 11/34 (2013.01 - KR)

Citation (examination)
US 4635234 A 19870106 - YAMAGUCHI TAKASHI [JP]

Cited by
EP0316082A3; EP0686975A1

Designated contracting state (EPC)
DE FR GB

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EP 0194939 A2 19860917; **EP 0194939 A3 19881221**; **EP 0194939 B1 19920205**; DE 3683783 D1 19920319; KR 860007744 A 19861017;
KR 910000876 B1 19910211; US 4802127 A 19890131

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EP 86400504 A 19860311; DE 3683783 T 19860311; KR 860001865 A 19860314; US 19677288 A 19880518